RENESAS

HD74LV1GT32A

2-input OR Gate / CMOS Logic Level Shifter

REJ03D0120-0900 Rev.9.00 Mar 21, 2008

Description

The HD74LV1GT32A is high-speed CMOS two input OR gate using silicon gate CMOS process. With CMOS low power dissipation, it provides high-speed equivalent to LS–TTL series. The internal circuit of three stages construction with buffer provides wide noise margin and stable output. The input protection circuitry on this device allows over voltage tolerance on the input, allowing the device to be used as a logic–level translator from 3.0 V CMOS Logic to 5.0 V CMOS Logic or from 1.8 V CMOS logic to 3.0 V CMOS Logic while operating at the high-voltage power supply. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

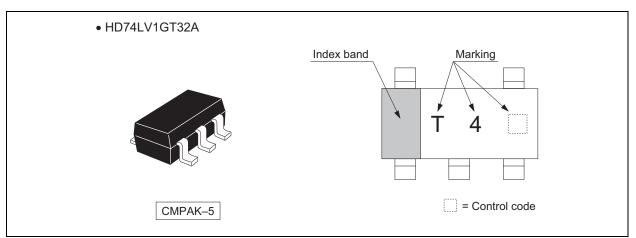
Features

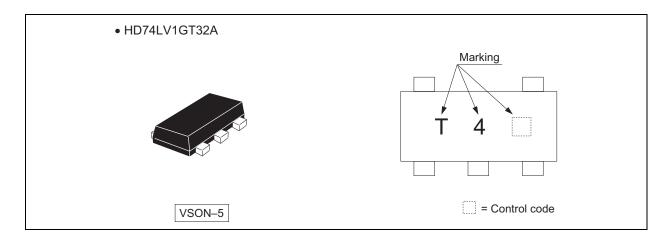
- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- TTL compatible input level. Supply voltage range : 3.0 to 5.5 V Operating temperature range : -40 to +85°C
- Logic-level translate function
 3.0 V CMOS logic → 5.0 V CMOS logic (@V_{CC} = 5.0 V)
 1.8 V or 2.5 V CMOS logic → 3.3 V CMOS logic (@V_{CC} = 3.3 V)
- All inputs V_{IH} (Max.) = 5.5 V (@V_{CC} = 0 V to 5.5 V) All outputs V₀ (Max.) = 5.5 V (@V_{CC} = 0 V)
- Output current ± 6 mA (@V_{CC} = 3.0 V to 3.6 V), ± 12 mA (@V_{CC} = 4.5 V to 5.5 V)
- All the logical input has hysteresis voltage for the slow transition.
- Ordering Information

Part Name	Package Type Package Code (Previous Code)		Package Abbreviation	Taping Abbreviation (Quantity)	
HD74LV1GT32ACME	CMPAK–5 pin	PTSP0005ZC-A (CMPAK-5V)	СМ	E (3000 pcs/reel)	
HD74LV1GT32AVSE	VSON–5 pin	PUSN0005KA-A (TNP-5DV)	VS	E (3000 pcs/reel)	

Note: Please consult the sales office for the above package availability.

Outline and Article Indication





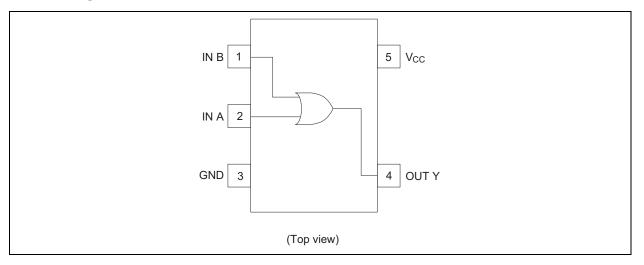
Function Table

Inp	Inputs						
A	В	Output Y					
L	L	L					
Н	L	н					
L	Н	Н					
Н	Н	Н					

H : High level

L : Low level

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	Vcc	-0.5 to 7.0	V	
Input voltage range ^{*1}	VI	-0.5 to 7.0	V	
	N.	–0.5 to V _{CC} + 0.5	V	Output : H or L
Output voltage range *1, 2	Vo	-0.5 to 7.0	v	V _{CC} : OFF
Input clamp current	l _{IK}	-20	mA	V ₁ < 0
Output clamp current	I _{OK}	±50	mA	$V_0 < 0$ or $V_0 > V_{CC}$
Continuous output current	I _O	±25	mA	$V_0 = 0$ to V_{CC}
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±50	mA	
Maximum power dissipation at Ta = 25°C (in still air) *3	PT	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. This value is limited to 5.5 V maximum.

3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	Vcc	3.0	5.5	V	
Input voltage range	VI	0	5.5	V	
Output voltage range	Vo	0	V _{CC}	V	
	L	—	6		V _{CC} = 3.0 to 3.6 V
	I _{OL}	—	12	mA	V_{CC} = 4.5 to 5.5 V
Output current		—	-6		V _{CC} = 3.0 to 3.6 V
	I _{OH}	—	-12		V_{CC} = 4.5 to 5.5 V
Input transition rise or fall rate	$\Delta t / \Delta v$	0	100	ns / V	V _{CC} = 3.0 to 3.6 V
Input transition rise or fall rate	Δι / Δν	0	20	115/V	V _{CC} = 4.5 to 5.5 V
Operating free-air temperature	Ta	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristic

• Ta = -40 to $85^{\circ}C$

ltem	Symbol	V _{cc} (V) *	Min	Тур	Max	Unit	Test condition
	VIH	3.0 to 3.6	1.5	_	_		
Input voltage	VIH	4.5 to 5.5	2.0	—	_	v	
input voltage	VIL	3.0 to 3.6		_	0.6	v	
	VIL	4.5 to 5.5	_	—	0.8		
	V _H	3.3	_	0.10	_	v	$V_{T}^{+} - V_{T}^{-}$
Hysteresis voltage	VН	5.0	_	0.15	_	v	$v_{T} - v_{T}$
	V _{он}	Min to Max	V _{CC} -0.1				I _{OH} = –50 μA
		3.0	2.48	—	_		I _{OH} = —6 mA
Output voltage		4.5	3.8	—	_	v	I _{OH} = –12 mA
Oulput voltage	V _{OL}	Min to Max	_	—	0.1		I _{OL} = 50 μA
		3.0	_	—	0.44		$I_{OL} = 6 \text{ mA}$
		4.5	_	—	0.55		I _{OL} = 12 mA
Input current	I _{IN}	0 to 5.5	—	—	±1	μΑ	$V_{IN} = 5.5 V \text{ or GND}$
Quiescent	I _{CC}	5.5	_		10	μA	$V_{IN} = V_{CC}$ or GND,
supply current	100	0.0			10	μΛ	$I_{O} = 0$
	ΔI_{CC}	5.5	_	_	1.5	mA	One input $V_{IN} = 3.4 V$,
		0.0					other input V _{CC} or GND
Output leakage current	I _{OFF}	0	_	_	5	μΑ	V_{IN} or $V_O = 0$ to 5.5 V
Input capacitance	CIN	5.0	—	2.5	—	pF	$V_{IN} = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

• $V_{CC} = 3.3 \pm 0.3 V$

Item	Symbol	٦	Га = 25°С	;	Ta = -40	to 85°C	Unit	Test	FROM	то
nem	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t _{PLH}	Ι	7.0	10.0	1.0	12.0		C _L = 15 pF	A or B	V
delay time	t _{PHL}		7.5	12.0	1.0	14.0	ns	C _L = 50 pF	AUID	T

• $V_{CC} = 5.0 \pm 0.5 \text{ V}$

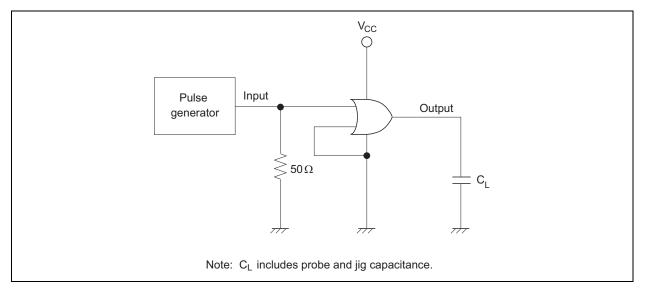
Item	Symbol	-	Га = 25°С	;	Ta = -40	to 85°C	Unit	Test	FROM	то
nem	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t _{PLH}	—	5.0	6.9	1.0	8.0	20	C∟ = 15 pF	A or B	v
delay time	t _{PHL}		5.5	7.9	1.0	9.0	ns	C∟ = 50 pF	AUB	I

Operating Characteristics

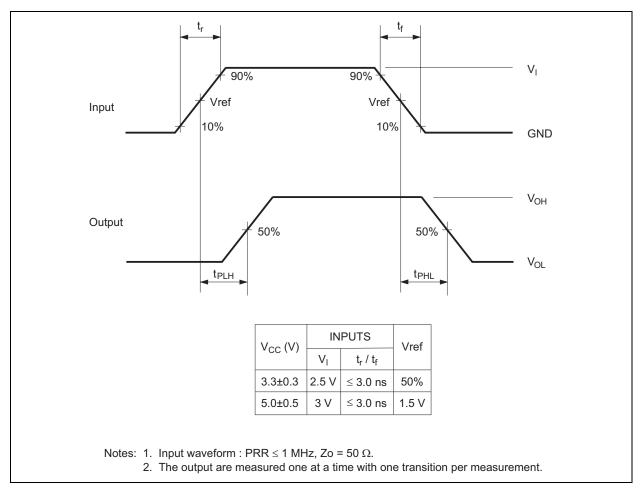
• $C_L = 50 \text{ pF}$

Item	Symbol	V _{cc} (V)		Ta = 25°C		Unit	Test Conditions
item	Symbol	VCC (V)	Min	Тур	Max	Unit	Test Conditions
Power dissipation capacitance	C _{PD}	5.0		11.5	_	pF	f = 10 MHz

Test Circuit

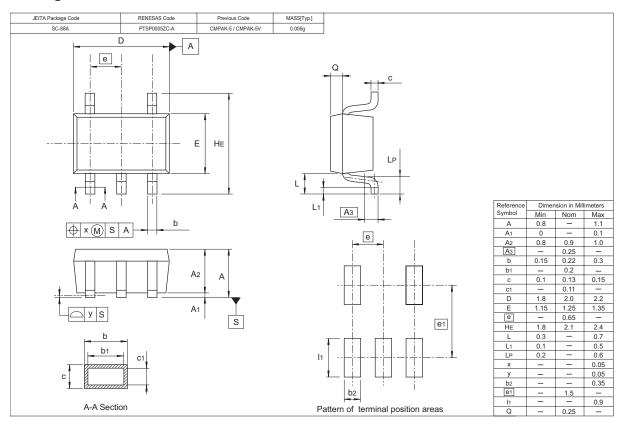


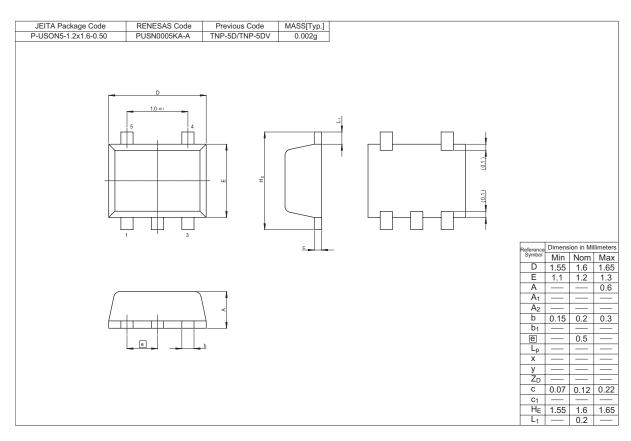
Waveforms



RENESAS

Package Dimensions





REJ03D0120-0900 Rev.9.00, Mar 21, 2008 Page 6 of 6 RENESAS

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- <section-header>

 Image: States

 Present States

 States

 Present State



http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd. 1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510